

P-Channel 60V(D-S) MOSFET

Product summary		
V_{DS}	-60	V
$R_{DS(ON)}$ (at $V_{GS}=-10V$) Typ.	80	$m\Omega$
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$) Typ.	109	$m\Omega$
$I_D(T_c=25^\circ C)$	-2.5	A

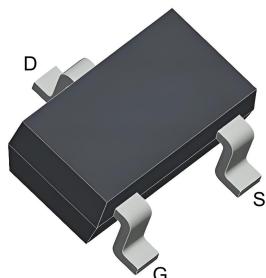
Features

- Advanced trench process technology
- High density cell design for ultra low on resistance

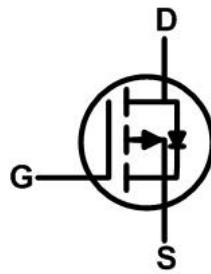
Applications

- Motor control
- Consumer electronic power supply

Pin Configuration



SOT-23



Packing Information

Device	Marking	Reel Size	Tape Width	Quantity
ECDA2203	B8P6	7"	8mm	3000pcs

Absolute Maximum Ratings (at $TA=25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current at $V_{GS}=-10V$	$T_A=25^\circ C$	-2.5
		$T_A=70^\circ C$	-2
I_{DM}	Pulse Drain Current Tested ^A	-10	A
P_D	Power Dissipation	$T_A=25^\circ C$	1.25
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Typical	Units
$R_{\theta JA}$	Thermal Resistance-Junction to ambient ^B	100	°C/W

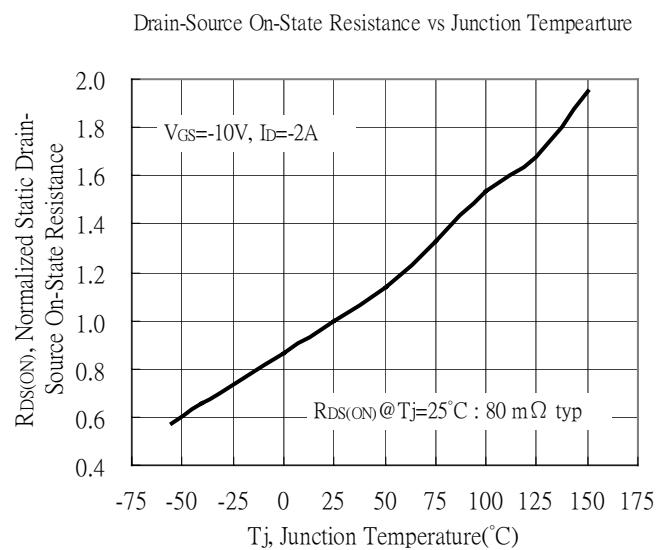
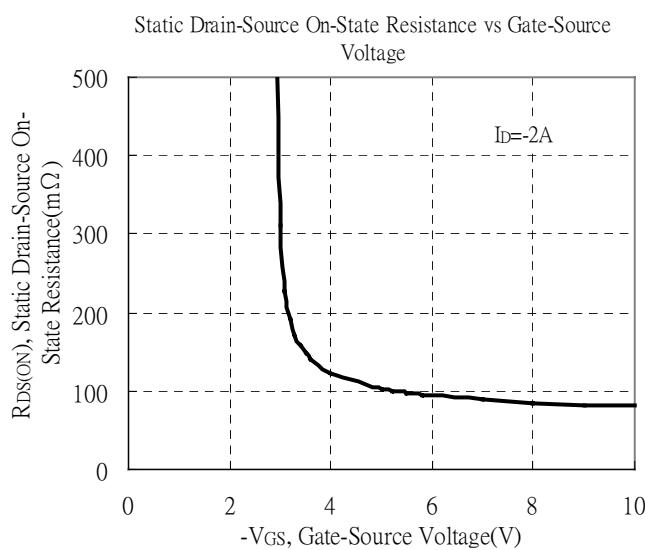
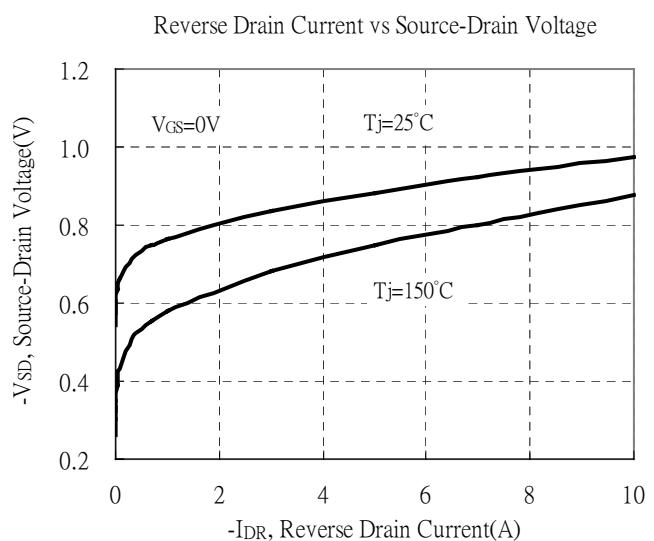
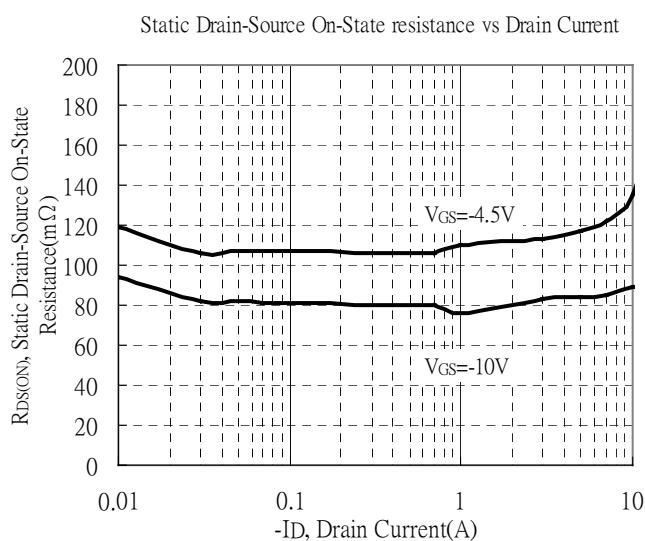
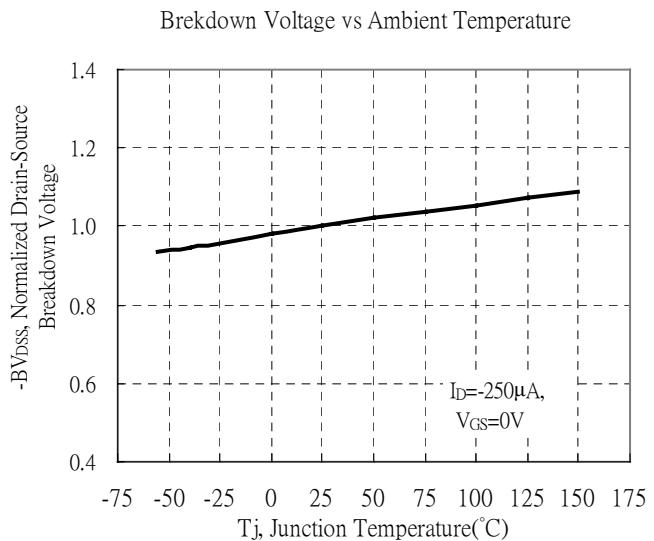
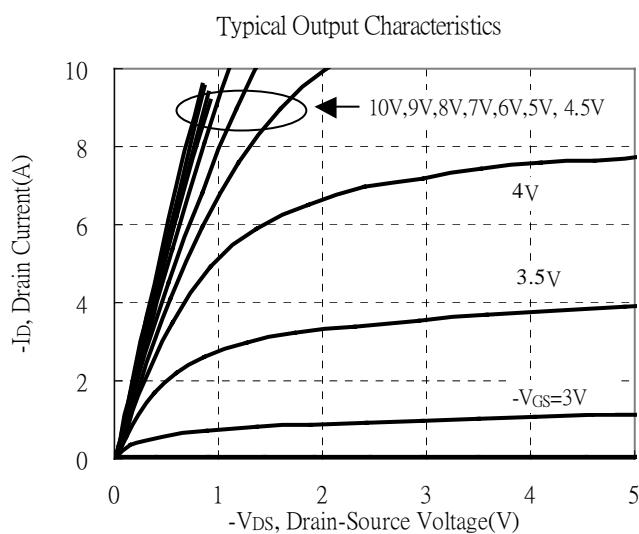
Electrical Characteristics (at $T_J = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
Static Parameters						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{\text{DS}}=-48\text{V}, V_{\text{GS}}=0\text{V}$	--	--	-1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 20\text{V}$	--	--	± 100	nA
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1.0	--	-2.5	V
$R_{\text{DS(ON)}}$	Drain-Source On-State Resistance	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-2\text{A}$	--	80	104	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-1.7\text{A}$	--	109	150	$\text{m}\Omega$
V_{SD}	Forward Voltage	$I_{\text{SD}}=-2\text{A}, V_{\text{GS}}=0\text{V}$	--	--	-1.2	V
Dynamic Parameters						
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=-25\text{V}$ $f=1\text{MHz}$	--	511	--	pF
C_{oss}	Output Capacitance		--	57	--	pF
C_{rss}	Reverse Transfer Capacitance		--	40	--	pF
Switching Parameters						
Q_g	Total Gate Charge	$V_{\text{DS}}=-48\text{V}, I_{\text{D}}=-2\text{A}$ $V_{\text{GS}}=-10\text{V}$	--	12	--	nC
Q_{gs}	Gate-Source Charge		--	1.7	--	nC
Q_{gd}	Gate-Drain Charge		--	3	--	nC
$t_{\text{D(on)}}$	Turn-on Delay Time	$V_{\text{DD}}=-30\text{V}$ $I_{\text{D}}=-2\text{A}, R_{\text{GEN}}=3\Omega$, $V_{\text{GS}}=-10\text{V}$	--	6.8	--	nS
t_r	Turn-on Rise Time		--	18.2	--	nS
$t_{\text{D(off)}}$	Turn-off Delay Time		--	26.4	--	nS
t_f	Turn-off Fall Time		--	7.6	--	nS
t_{rr}	Reverse recovery time	$I_{\text{F}}=-2\text{A}$, $di/dt=100 \text{ A/uS}$	--	10.7	--	nS
Q_{rr}	Reverse recovery charge		--	6.4	--	nC

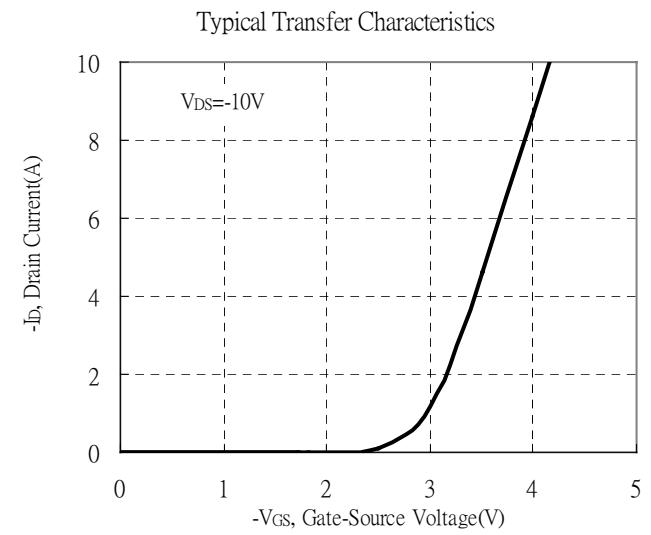
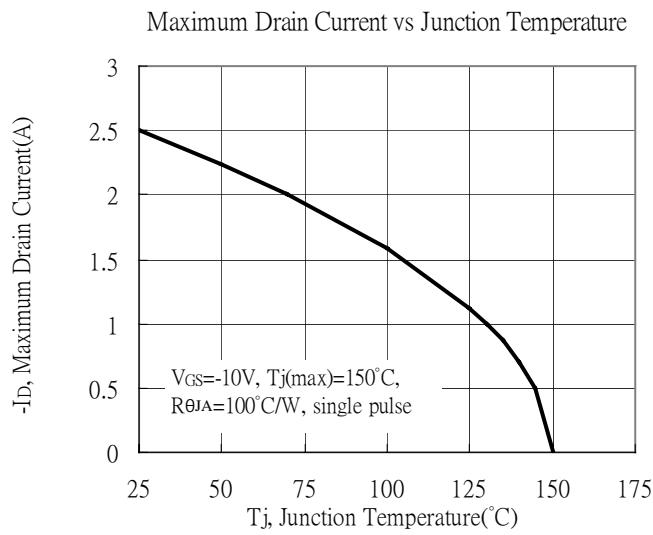
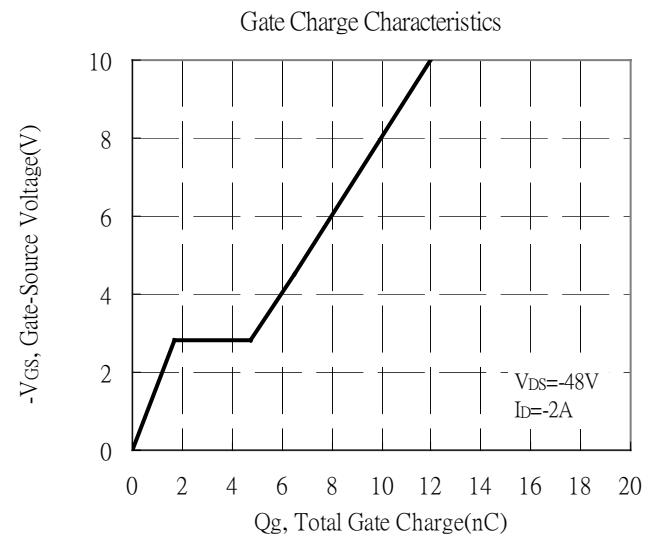
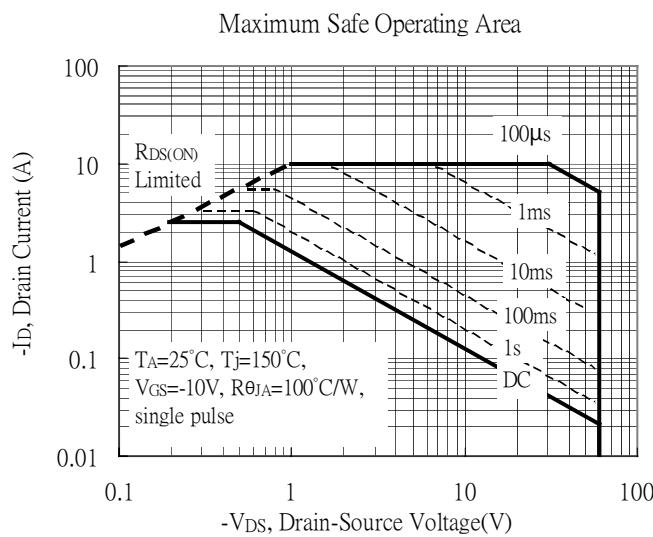
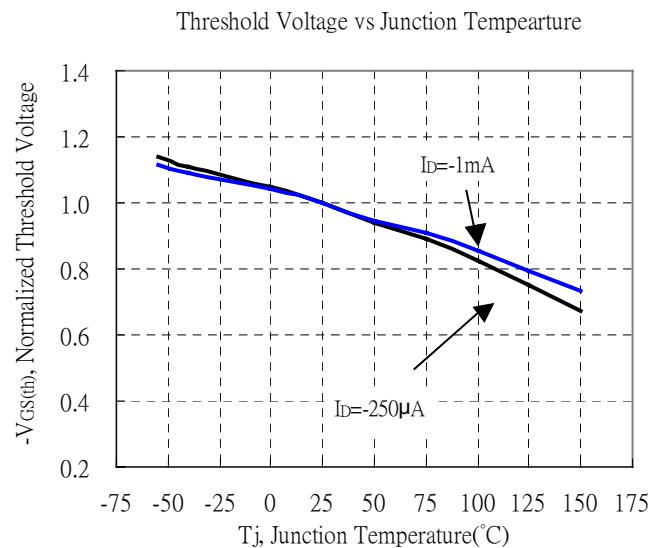
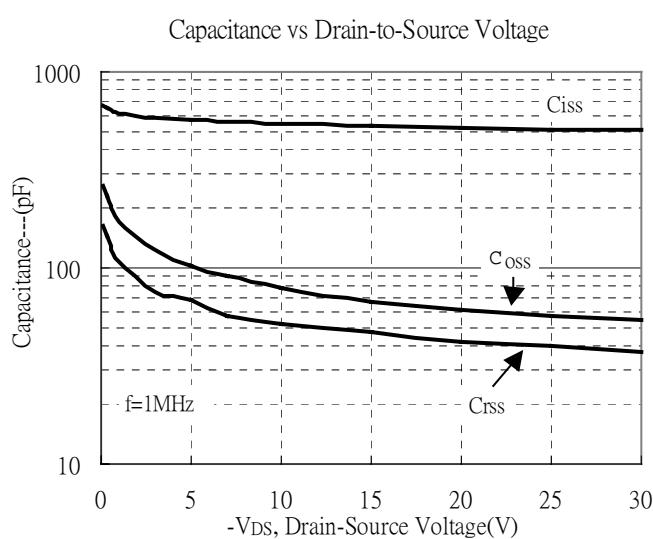
A. Pulse Test: Pulse Width $\leq 300\text{us}$, Duty cycle $\leq 2\%$.

B. Device mounted on FR-4 PCB, 1 inch x 1 inch x 0.062 inch.

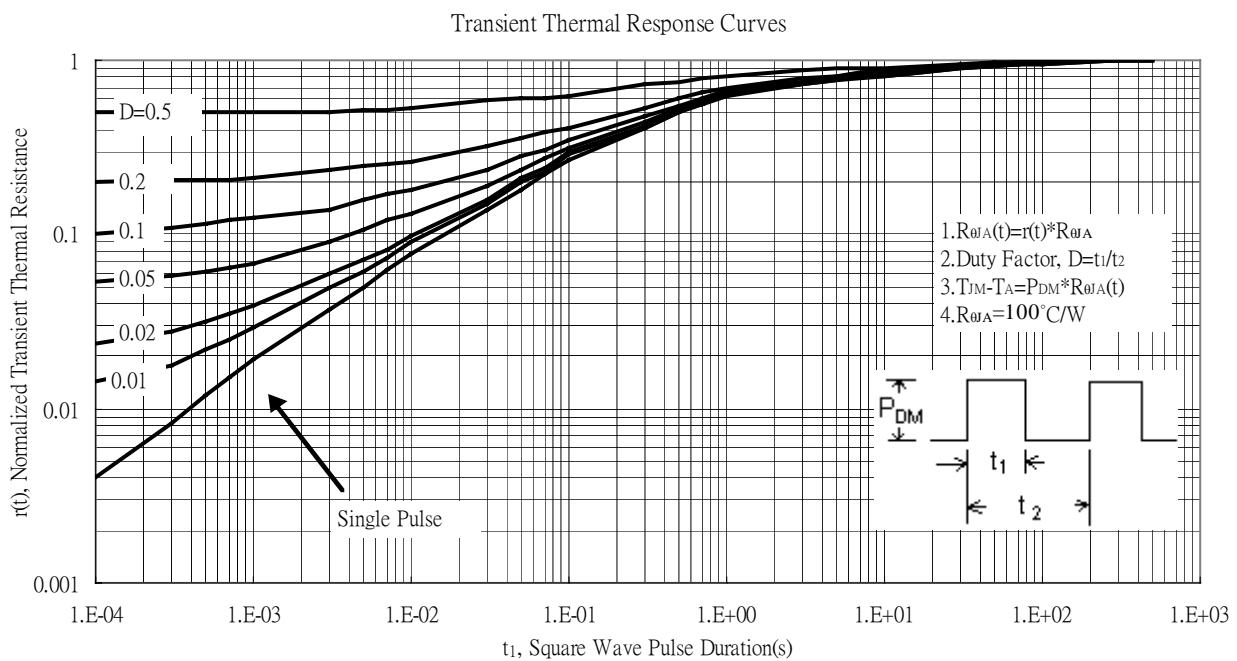
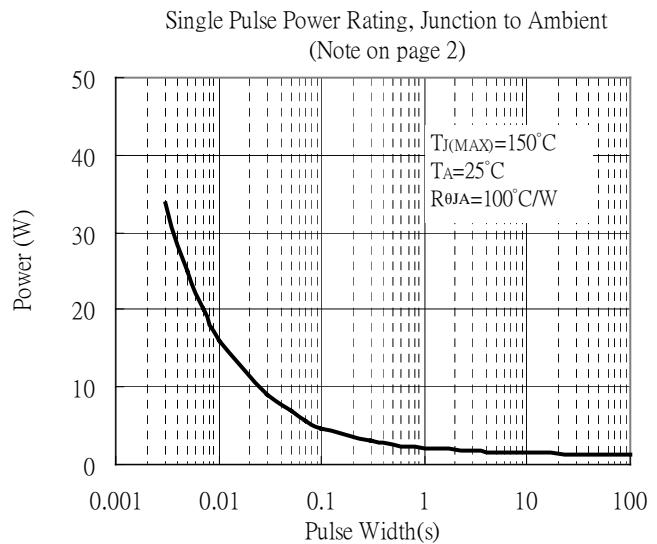
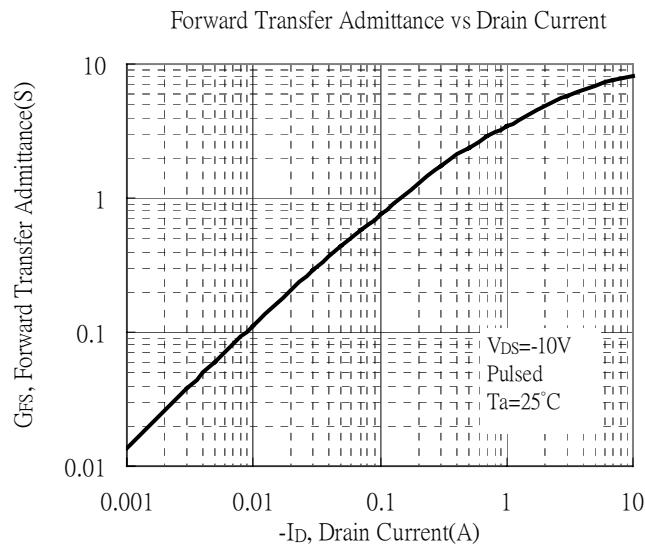
Typical Characteristics



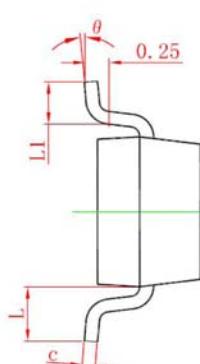
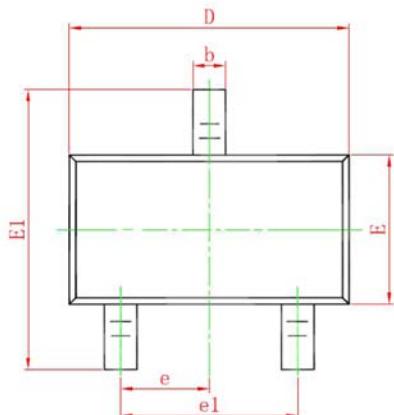
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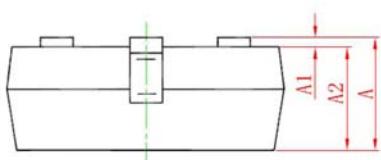
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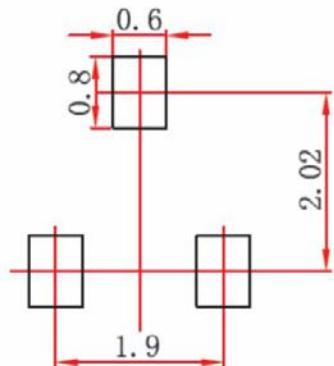
SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°



Recommended Pad outline



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.